

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		User Part Number						
		PDTC143XQA						
		Part Description						
		Nexperia DHAM	polar Transistor					
		MCD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC Preconditioning	Soak Tamb = 85 °C, RH = 85% Reflow soldering	168 hours 3 cycles			_		
# A1	Preconditioning		3 cycles	208	16640	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
4 D 1	Bias	Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage	1000 hours	202	16160	0		
# B1	Dias	reverse voltage	1000 nours	202	10100	U		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Timax, not to exceed 150°C	1000 cycles	52	4160	0		
π A-T	. , ,	IESD22-A102	1000 cycles	32	1100			
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	52	4160	0		
	НЗТ В	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
£ A2 alt	Temperature Reverse Bias	rated reverse voltage ^[1]	1000 hours	52	4160	0		
		MIL-STD-750 Method 1037						
	IOL	ton = toff, devices powered to insure ΔTj =						
£ A5	Intermittent Operating Life	100 °C for 15000 cycles	1000 hours	52	4160	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.		
	SD Caldonahilitus	1 CTD 003						
# C10	Solderability	J-STD-002		111	1110	0		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

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